

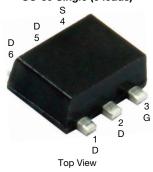
Vishay Siliconix



N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (TYP.)		
	0.142 at V _{GS} = 10 V	1.02			
30	0.154 at V _{GS} = 4 V	0.98	1.5		
	0.195 at V _{GS} = 2.5 V	0.87			

SC-89 Single (6 leads)



Marking Code: D **Ordering Information:**

Si1078X-T1-GE3 (lead (Pb)-free and halogen-free)

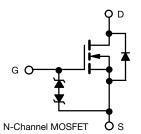
FEATURES

- TrenchFET® power MOSFET
- 100 % R_g tested
- Typical ESD performance 1400 V
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

· Load switch for portable devices



PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V_{DS}	30	7/		
Gate-Source Voltage		V _{GS}	± 12	V	
O	T _A = 25 °C		1.02 ^{a, b}		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	l _D	0.82 ^{a, b}		
Pulsed Drain Current (t = 100 μs)		I _{DM}	6	A	
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	0.2 ^{a, b}		
Martin or Brown Black attack	T _A = 25 °C	_	0.24 ^{a, b}	14/	
Maximum Power Dissipation	T _A = 70 °C	P _D	0.15 ^{a, b}	W	
Operating Junction and Storage Temperature R	ange	T _J , T _{stq}	-55 to +150	°C	

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT			
Maximum Junction-to-Ambient ^{a, c}	t ≤ 5 s	Ь	440	530	°C/W		
Maximum Junction-to-Ambient, -	Steady State	R _{thJA}	540	650	C/VV		

Notes

- a. Surface mounted on 1" x 1" FR4 board.
- b. t = 5 s.
- c. Maximum under steady state conditions is 650 °C/W.



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			ı			l	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30	-	-	V	
V _{DS} Temperature Coefficient	e Coefficient ΔV _{DS} /T _J		-	36.7	-		
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	-	-2.8	-	mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6	-	1.5	V	
0.1.0		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	-	-	± 20		
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$	2 V	± 1	1 ,		
Zana Oata Wallana Buria Oanaal		V _{DS} = 30 V, V _{GS} = 0 V	-	-	1	μA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 85 °C	-	-	10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	6	-	-	Α	
		V _{GS} = 10 V, I _D = 1 A	-	0.118	0.142		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 1 \text{ A}$	-	0.128	0.154	Ω	
	, ,	$V_{GS} = 2.5 \text{ V}, I_D = 0.5 \text{ A}$	-	0.150	0.195		
Forward Transconductance	9 _{fs}	V _{DS} = 15 V, I _D = 1 A	-	5.5	-	S	
Dynamic ^b			•			•	
Input Capacitance	C _{iss}		-	110	-	pF	
Output Capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	-	21	-		
Reverse Transfer Capacitance	C _{rss}		-	11	-		
Table Oaks Observe	Qg	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 1 A	-	3	6		
Total Gate Charge			-	1.5	3	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 1 \text{ A}$	-	0.2	-		
Gate-Drain Charge	Q _{gd}		-	0.42	-		
Gate Resistance	Rg	f = 1 MHz	1.04	5.2	5.6	Ω	
Turn-On Delay Time	t _{d(on)}		-	8	16		
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_L = 18.9 \Omega$		25	38		
Turn-Off Delay Time	t _{d(off)}			23	35		
Fall Time	t _f		-	23	35	ns	
Turn-On Delay Time	t _{d(on)}		-	5	10		
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_L = 18.9 \Omega$	-	23	35		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 0.8 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	10	20		
Fall Time	t _f		-	35	53		
Drain-Source Body Diode Characteris	tics						
Pulse Diode Forward Current ^a	I _{SM}		-	-	6	Α	
Body Diode Voltage	V _{SD}	I _S = 0.8 A	-	0.75	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}		-	12	20	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	L = 2 A dl/d+ 100 A/:-	-	4	8	nC	
Reverse Recovery Fall Time	ta	I _F = 2 A, dl/dt = 100 A/μs	-	7	-		
Reverse Recovery Rise Time	t _b		-	5	-	ns	

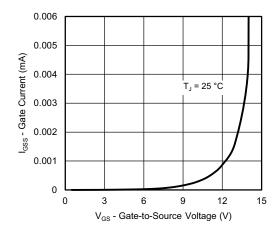
Notes

- a. Pulse test; pulse width $\leq 100~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

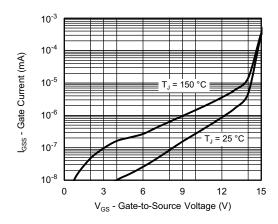
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



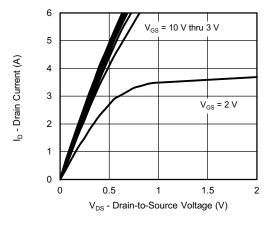
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



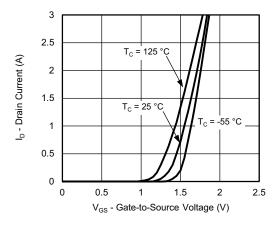
Gate Current vs. Gate-to-Source Voltage



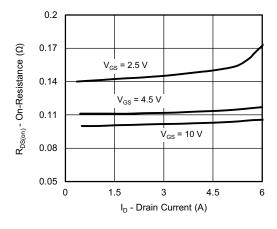
Gate Current vs. Gate-to-Source Voltage



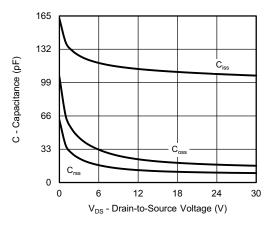
Output Characteristics



Transfer Characteristics



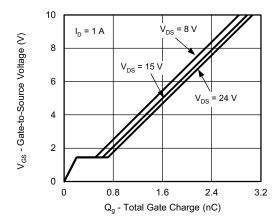
On-Resistance vs. Drain Current



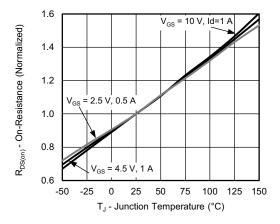
Capacitance



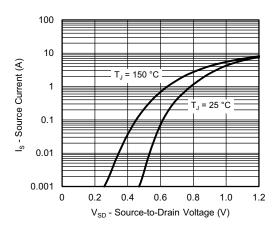
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



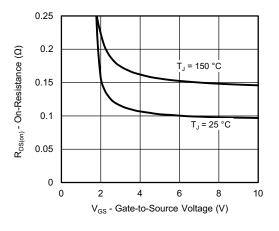
Gate Charge



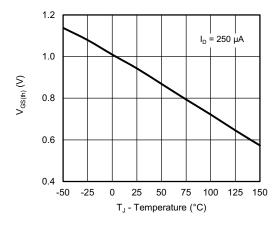
On-Resistance vs. Junction Temperature



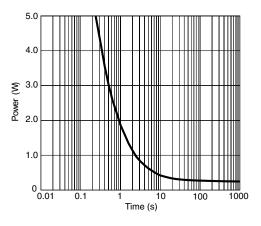
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



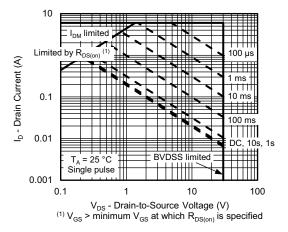
Threshold Voltage



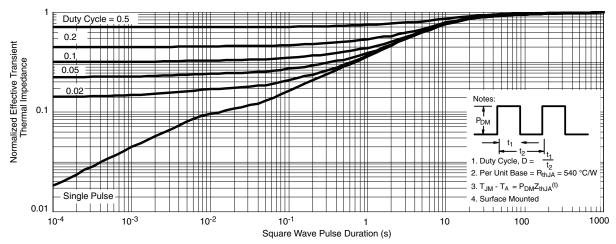
Single Pulse Power, Junction-to-Ambient



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient

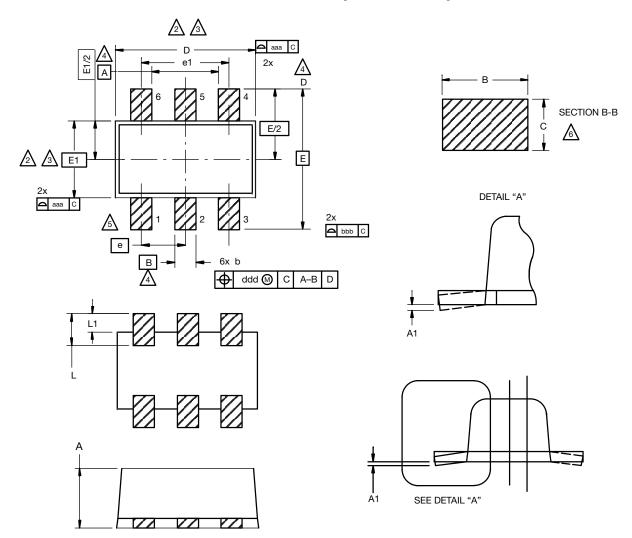


Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68549.



SC-89 6-Leads (SOT-563F)



Notes

1. Dimensions in millimeters.

Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

ADatums A, B and D to be determined 0.10 mm from the lead tip.

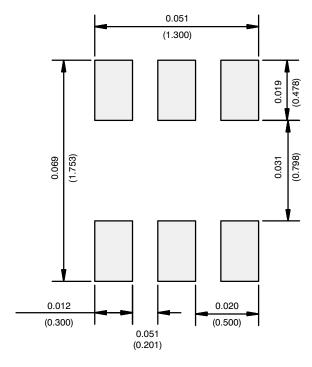
A Terminal numbers are shown for reference only.

These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS					
DIW.	MIN.	NOM.	MAX.			
Α	0.56	0.58	0.60			
A1	0	0.02	0.10			
b	0.15	0.22	0.30			
С	0.10	0.14	0.18			
D	1.50	1.60	1.70			
E	1.50	1.60	1.70			
E1	1.15	1.20	1.25			
е	0.45	0.50	0.55			
e1	0.95	1.00	1.05			
L	0.25	0.35	0.50			
L1	0.10	0.20	0.30			
C14-0439-Rev. C, 11-Aug-14 DWG: 5880						



RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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